S8550LT1 PNP EPITAXIAL SILICON TRANSISTORS

HIGH VOLTAGE TRANSISTOR: (PNP)

SOT—23

1. BASE
2. EMITTER
3. COLLECTOR

FEATURES

Die Size

0.44*0.44mm

Power dissipation

P_{CM} : 225mW（ Tamb=25℃ ）

Collector current

I_{CM} : 0.5A

Collector-base voltage

$V_{(BR)CBO}$: 40V

ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V(BR)_{CBO}$	Ic= 100μA , I_E=0	30			V
Collector-emitter breakdown voltage	$V(BR)_{CEO}$	Ic= 1 mA， I_B=0	21			V
Emitter-base breakdown voltage	$V(BR)_{EBO}$	I_E= 100μA， I_C=0	5.0			V
Collector cut-off current	I_{CBO}	V_{CB}= 30V , I_E=0			1.0	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 5V， I_C=0			100	nA
DC current gain	$H_{FE(1)}$	V_{CE}= 1V, I_C= 150mA	120		400	
	$H_{FE(2)}$	V_{CE}= 1V, I_C= 500mA	40			
Collector-emitter saturation voltage	V_{CE}(sat)	I_C= 500mA, I_B= 50 mA			500	mV
Base-emitter saturation voltage	V_{BE}(sat)	I_C= 500mA, I_B= 50 mA			1.2	V
Base-emitter voltage	$V_{BE(on)}$	I_C= 10mA, V_{CE} =1V			1.0	V

CLASSIFICATION OF $H_{FE(1)}$

Rank	B9C	B9D	B9E
Range	120-200	160-300	280-400

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